

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ P6

600V CoolMOS™ P6 Power Transistor
IPx60R099P6

Data Sheet

Rev. 2.1
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ P6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

Features

- Increased MOSFET dv/dt ruggedness
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

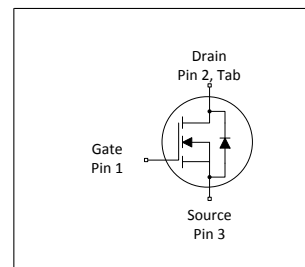
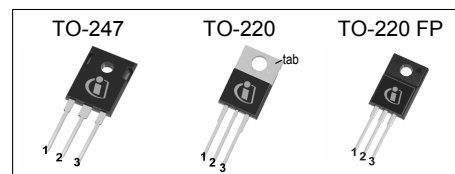


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	99	mΩ
$Q_{g,typ}$	70	nC
$I_{D,pulse}$	109	A
$E_{oss@400V}$	8.8	μJ
Body diode di/dt	300	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPW60R099P6	PG-TO 247	6R099P6	see Appendix A
IPP60R099P6	PG-TO 220		
IPA60R099P6	PG-TO 220 FullPAK		

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	37.9 24.0	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	109	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	796	mJ	$I_D=6.6\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	1.21	mJ	$I_D=6.6\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, repetitive	I_{AR}	-	-	6.6	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation (Non FullPAK) TO-220, TO-247	P_{tot}	-	-	278	W	$T_C=25^\circ\text{C}$
Power dissipation (FullPAK) TO-220FP	P_{tot}	-	-	34	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque (Non FullPAK) TO-220, TO-247	-	-	-	60	Ncm	M3 and M3.5 screws
Mounting torque (FullPAK) TO-220FP	-	-	-	50	Ncm	M2.5 screws
Continuous diode forward current	I_S	-	-	32.9	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	109	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	300	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage for TO-220FP	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics (Non FullPAK) TO-220, TO-247

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.45	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

Table 4 Thermal characteristics (FullPAK) TO-220FP

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.65	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0\text{V}$, $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	$V_{DS}=V_{GS}$, $I_D=1.21\text{mA}$
Zero gate voltage drain current	I_{DSS}	-	-	5	μA	$V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $V_{DS}=600$, $V_{GS}=0\text{V}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.089 0.232	0.099 -	Ω	$V_{GS}=10\text{V}$, $I_D=14.5\text{A}$, $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$, $I_D=14.5\text{A}$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	1	-	Ω	$f=1\text{MHz}$, open drain

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	3330	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$
Output capacitance	C_{oss}	-	140	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$, $f=1\text{MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	110	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	495	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=18.1\text{A}$, $R_G=1.7\Omega$; see table 9
Rise time	t_r	-	10	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=18.1\text{A}$, $R_G=1.7\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	50	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=18.1\text{A}$, $R_G=1.7\Omega$; see table 9
Fall time	t_f	-	5	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=18.1\text{A}$, $R_G=1.7\Omega$; see table 9

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	20	-	nC	$V_{DD}=400\text{V}$, $I_D=18.1\text{A}$, $V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	24	-	nC	$V_{DD}=400\text{V}$, $I_D=18.1\text{A}$, $V_{GS}=0$ to 10V
Gate charge total	Q_g	-	70	-	nC	$V_{DD}=400\text{V}$, $I_D=18.1\text{A}$, $V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	6.1	-	V	$V_{DD}=400\text{V}$, $I_D=18.1\text{A}$, $V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=18.1A$, $T_J=25^{\circ}C$
Reverse recovery time	t_{rr}	-	470	-	ns	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	9	-	μC	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	37	-	A	$V_R=400V$, $I_F=18.1A$, $di_F/dt=100A/\mu s$; see table 8

5 Electrical characteristics diagrams

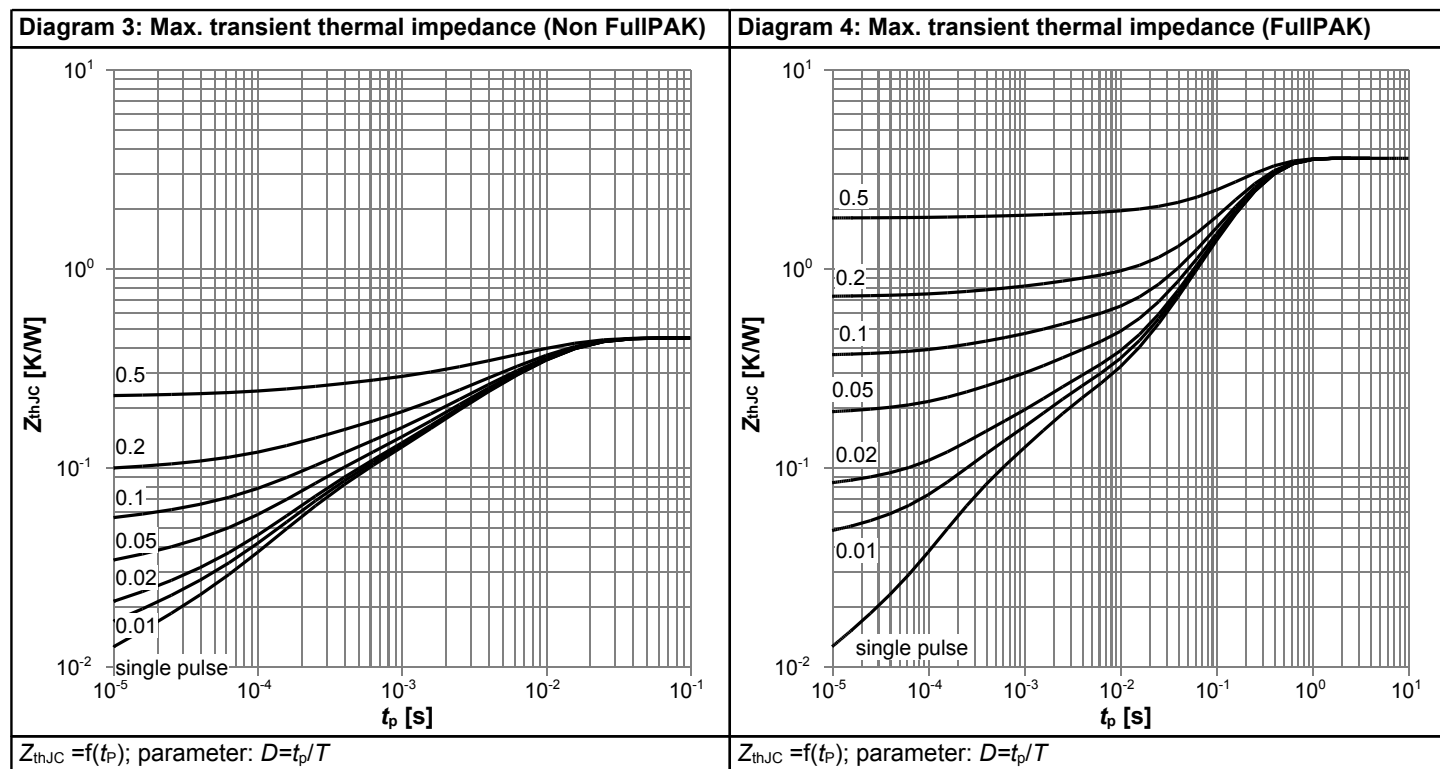
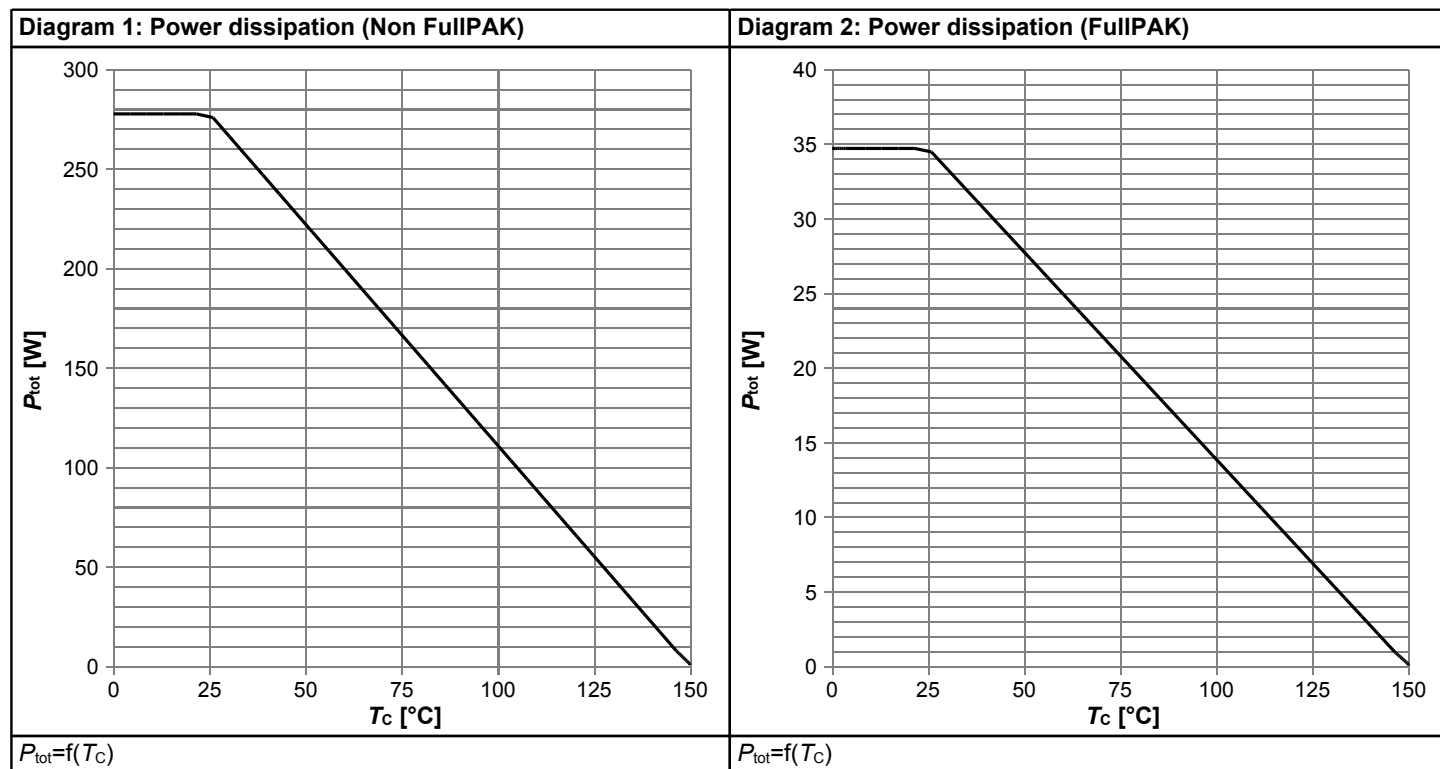
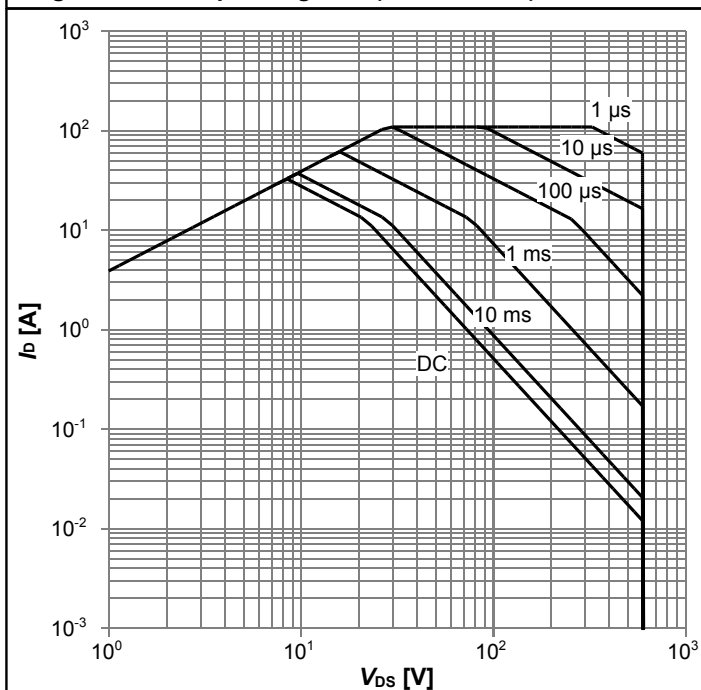
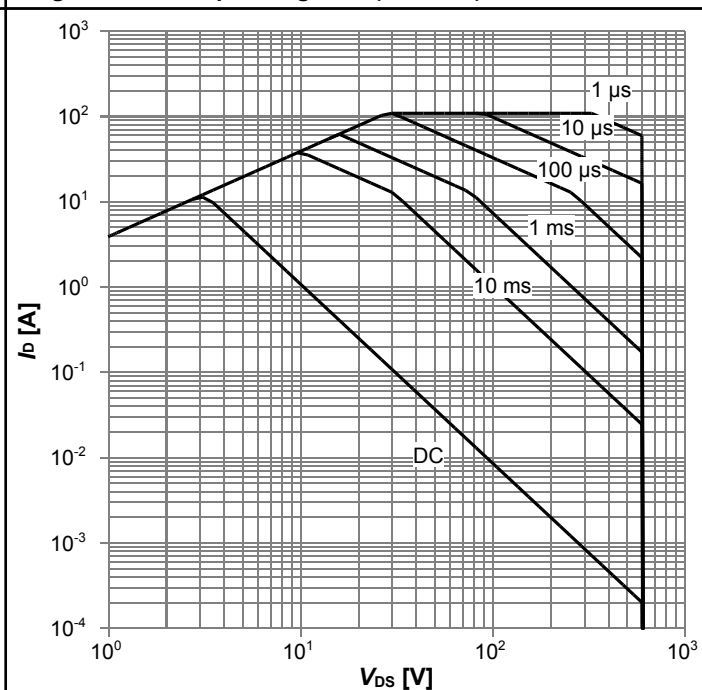


Diagram 5: Safe operating area (Non FullPAK)



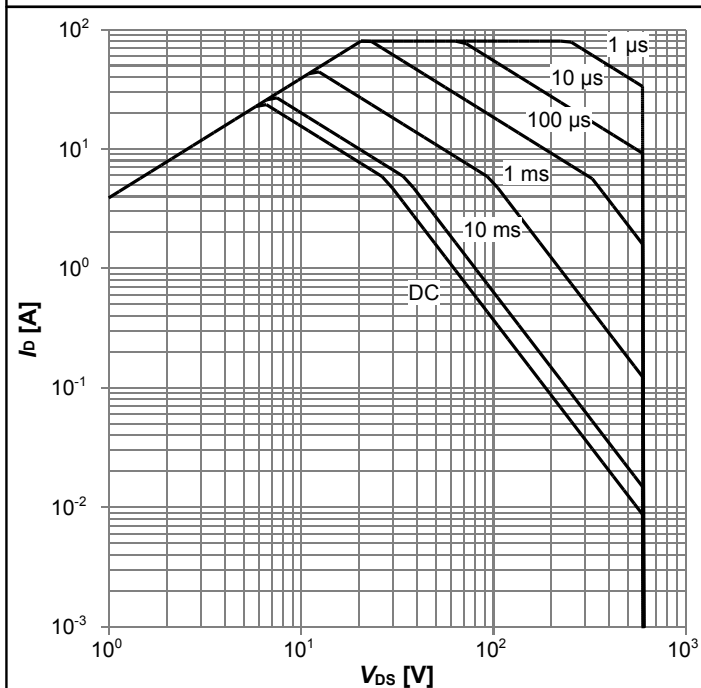
$I_D=f(V_{DS})$; $T_C=25\text{ °C}$; $D=0$; parameter: t_p

Diagram 6: Safe operating area (FullPAK)



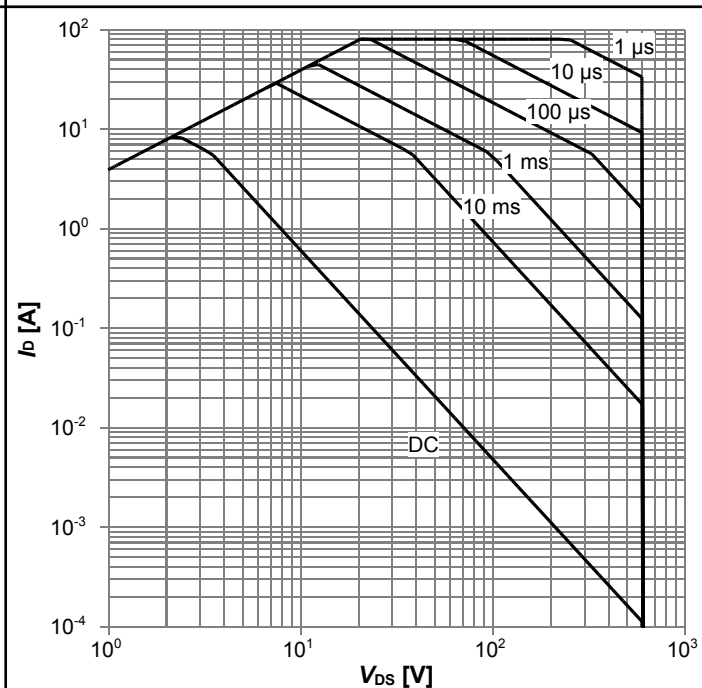
$I_D=f(V_{DS})$; $T_C=25\text{ °C}$; $D=0$; parameter: t_p

Diagram 7: Safe operating area (Non FullPAK)



$I_D=f(V_{DS})$; $T_C=80\text{ °C}$; $D=0$; parameter: t_p

Diagram 8: Safe operating area (FullPAK)



$I_D=f(V_{DS})$; $T_C=80\text{ °C}$; $D=0$; parameter: t_p

Diagram 9: Typ. output characteristics

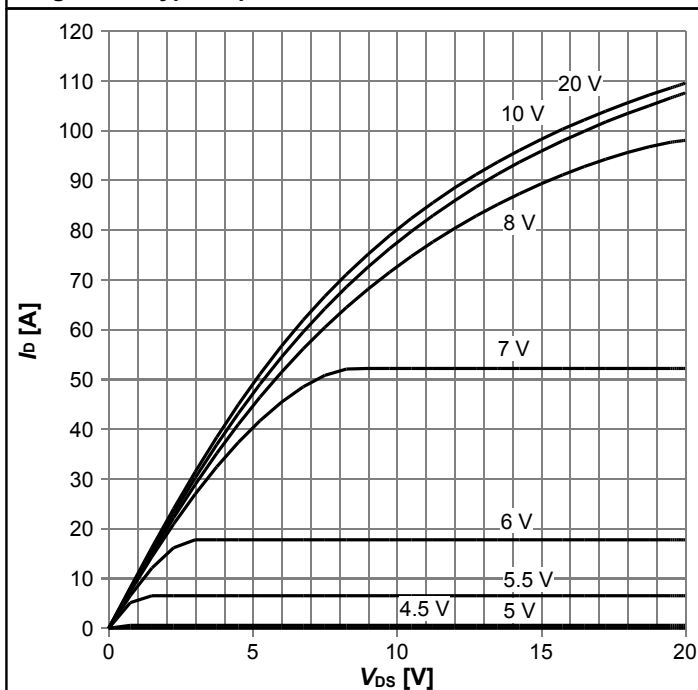

 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 10: Typ. output characteristics

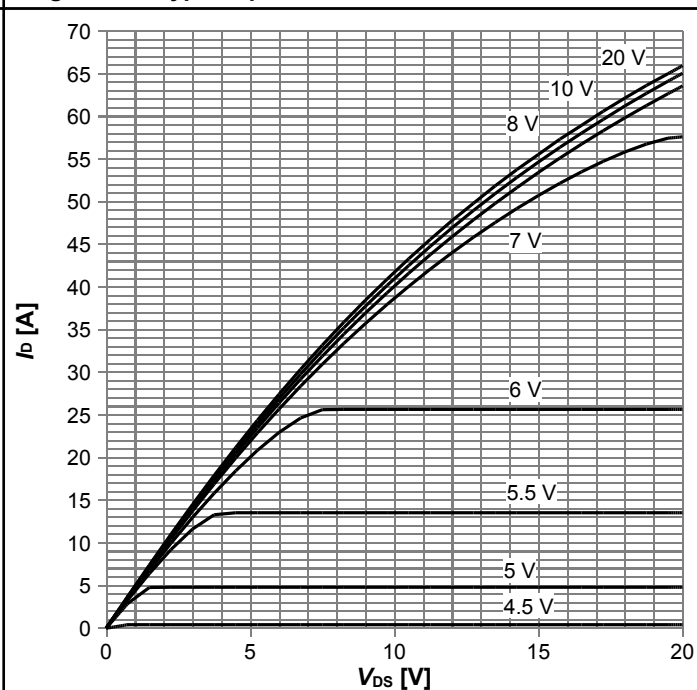

 $I_D = f(V_{DS}); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 11: Typ. drain-source on-state resistance

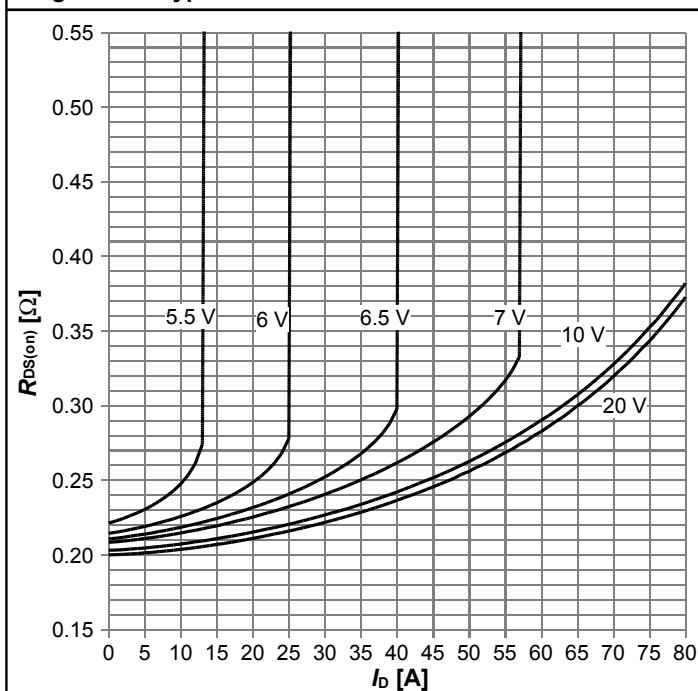

 $R_{DS(on)} = f(I_D); T_J = 125^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 12: Drain-source on-state resistance

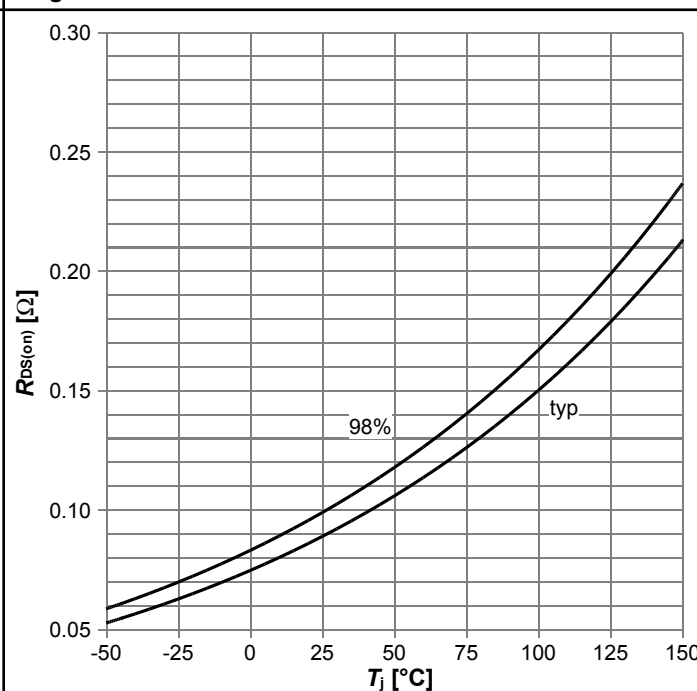

 $R_{DS(on)} = f(T_J); I_D = 14.5\text{ A}; V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics

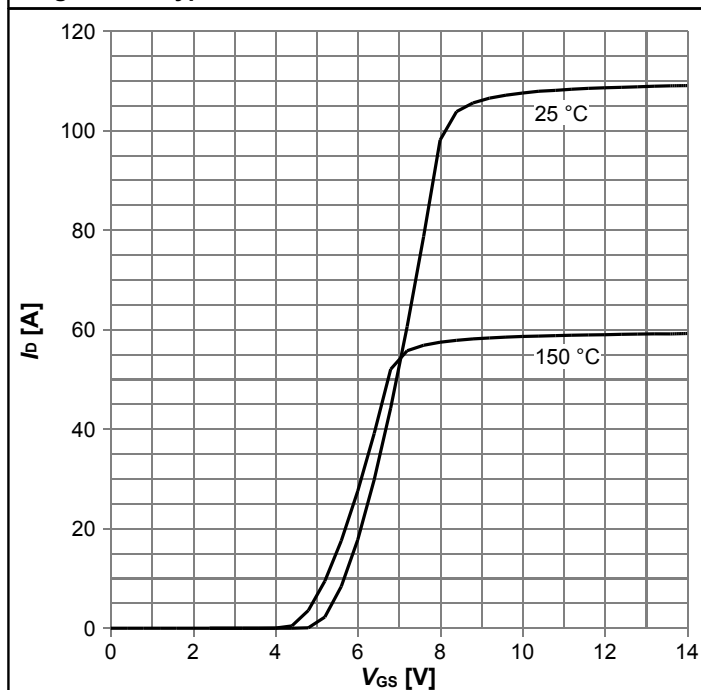

 $I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 14: Typ. gate charge

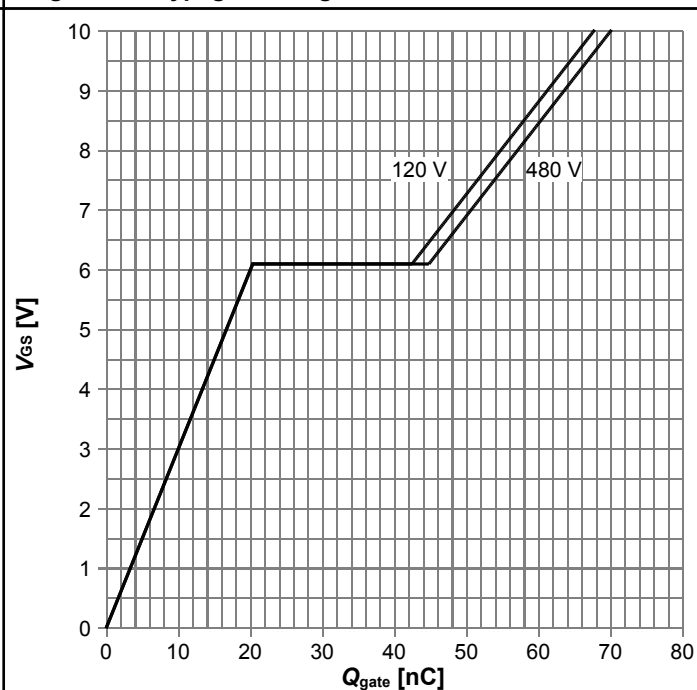

 $V_{GS} = f(Q_{gate}); I_D = 18.1 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 15: Forward characteristics of reverse diode

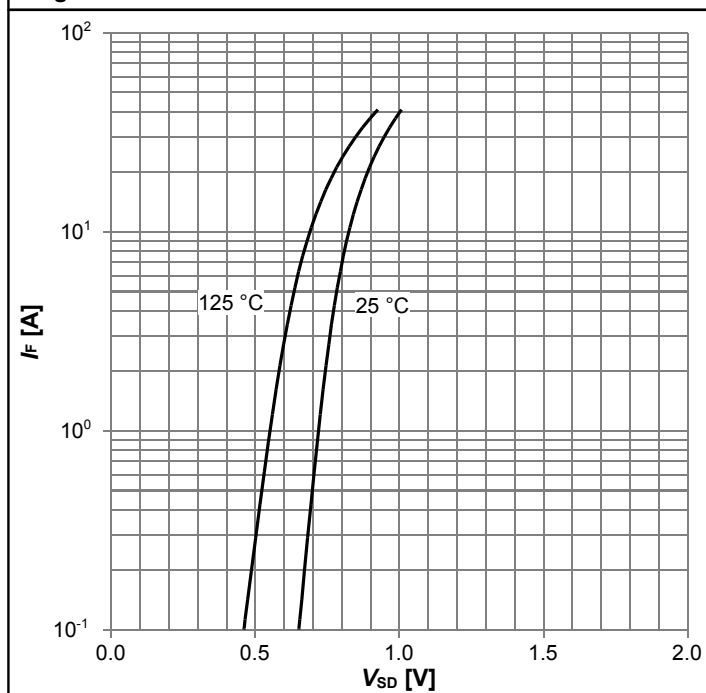

 $I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 16: Avalanche energy

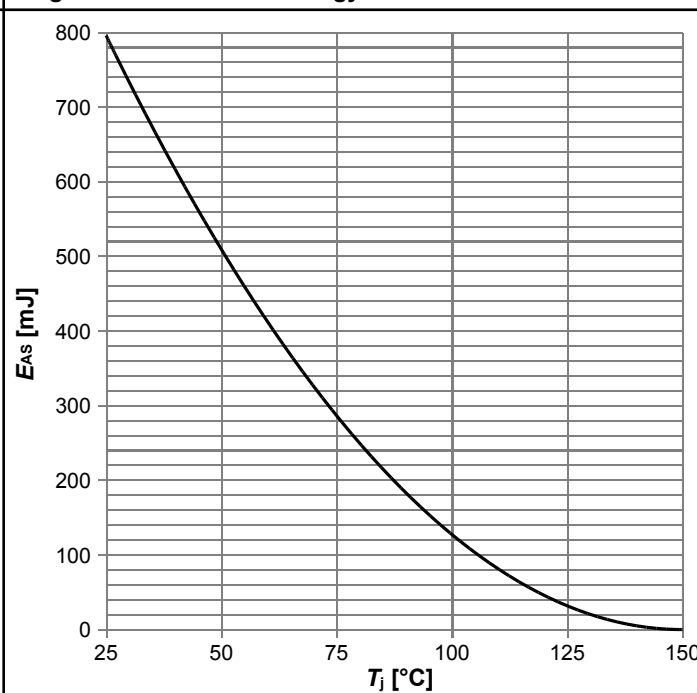
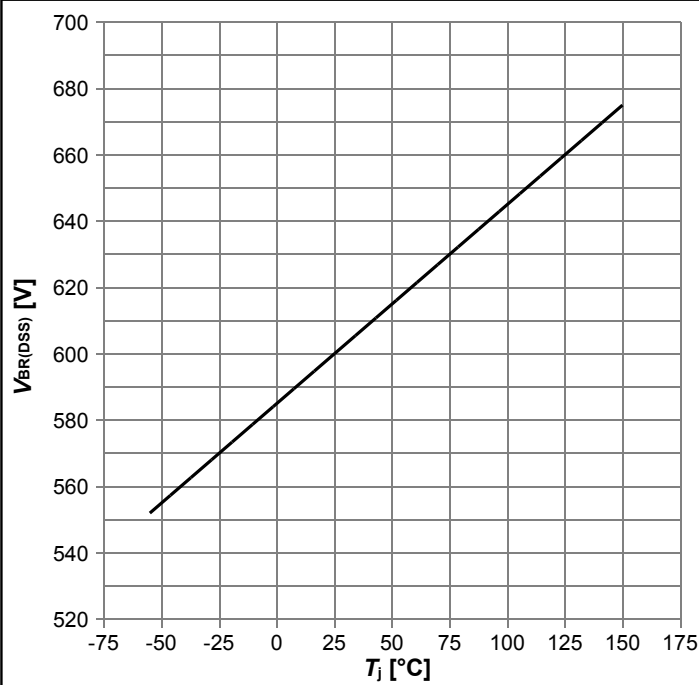
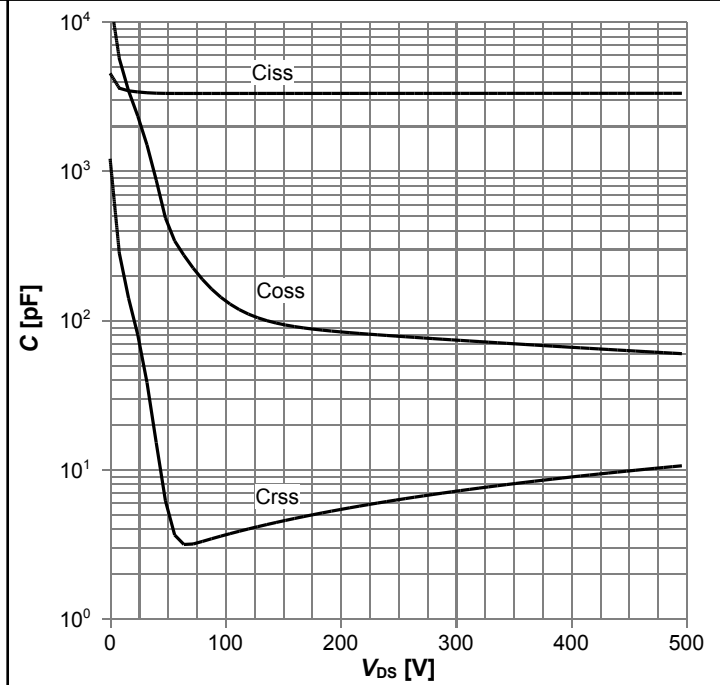

 $E_{AS} = f(T_j); I_D = 6.6 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 17: Drain-source breakdown voltage



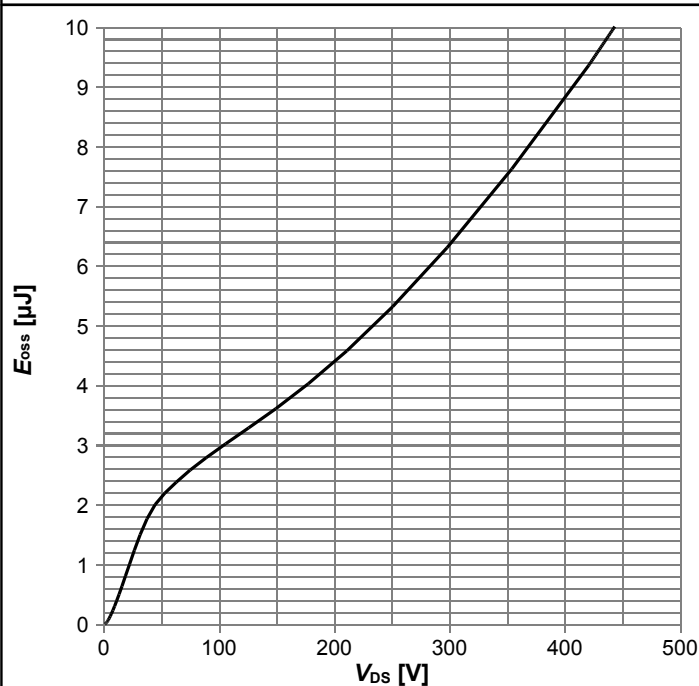
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 18: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 19: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

6 Test Circuits

Table 9 Diode characteristics

Test circuit for diode characteristics $R_{g1} = R_{g2}$	Diode recovery waveform $t_{rr} = t_F + t_S$ $Q_{rr} = Q_F + Q_S$
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Table 10 Switching times

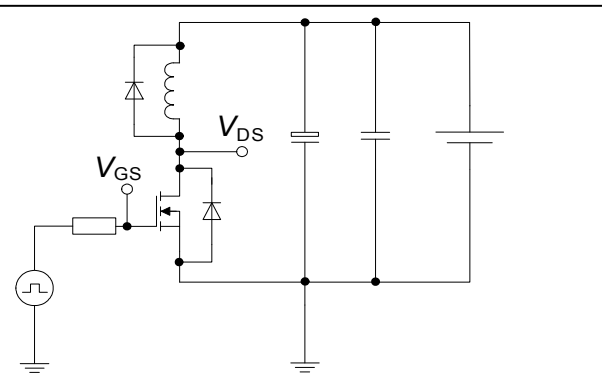
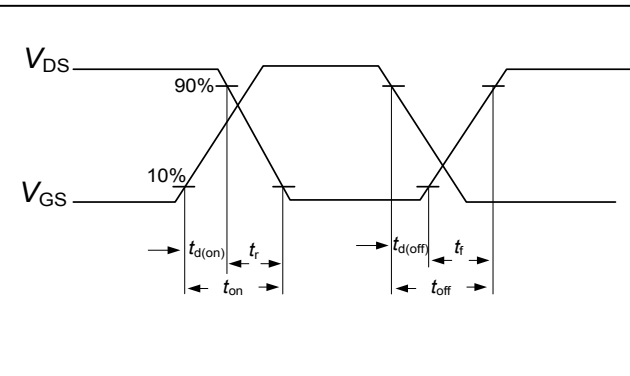
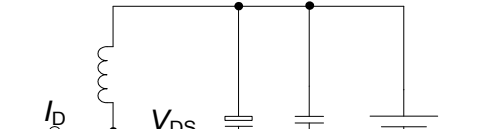
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The gate voltage is labeled V_{GS}. The MOSFET's drain is connected to a DC source and an inductive load (represented by an inductor and a diode in parallel). The drain voltage is labeled V_{DS}. A load capacitor is connected in parallel with the inductive load to simulate a realistic load. The MOSFET's body diode is also shown.	 The timing diagram shows the switching waveforms for V_{DS} (drain-source voltage) and V_{GS} (gate-source voltage). The diagram illustrates the turn-on and turn-off transitions. Key time intervals are marked: $t_{d(on)}$: Delay time from the start of the gate voltage rise to the 90% rise of the drain voltage. t_r: Rise time of the drain voltage from 90% to 100%. t_{on}: Total turn-on time from the start of the gate voltage rise to the end of the drain voltage rise. $t_{d(off)}$: Delay time from the start of the gate voltage fall to the 90% fall of the drain voltage. t_f: Fall time of the drain voltage from 90% to 100%. t_{off}: Total turn-off time from the start of the gate voltage fall to the end of the drain voltage fall.

Table 11 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines

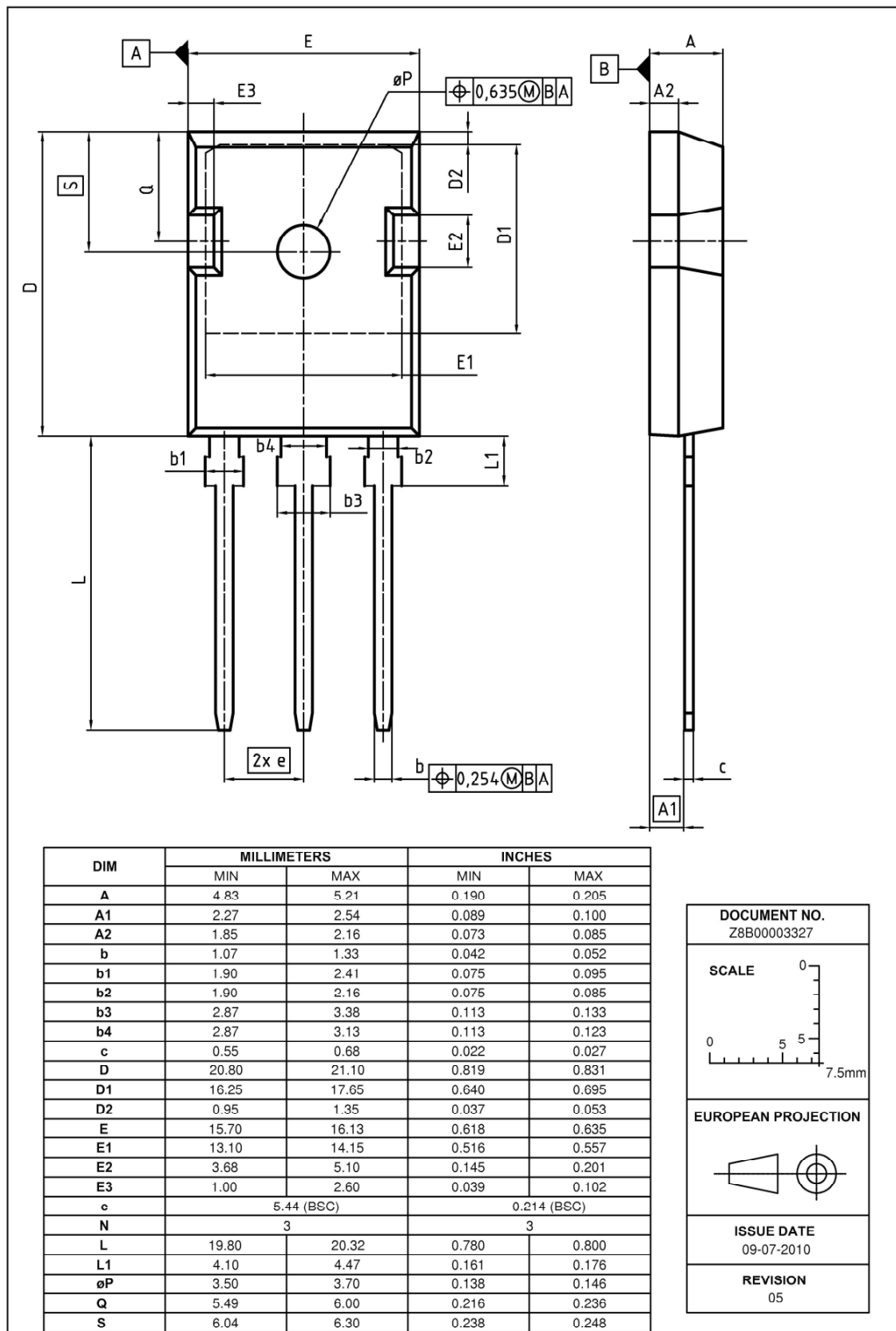


Figure 1 Outline PG-TO 247, dimensions in mm/inches

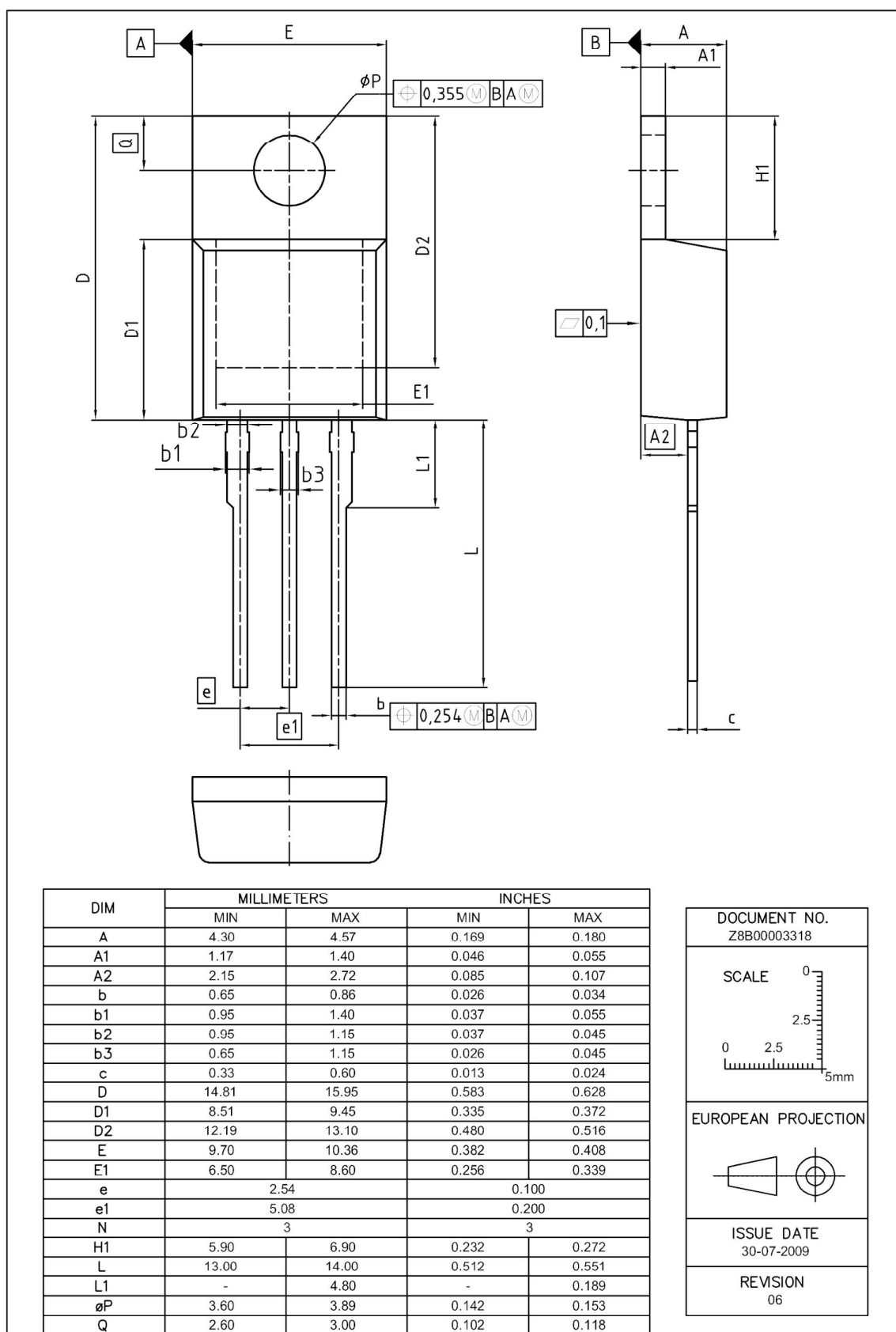
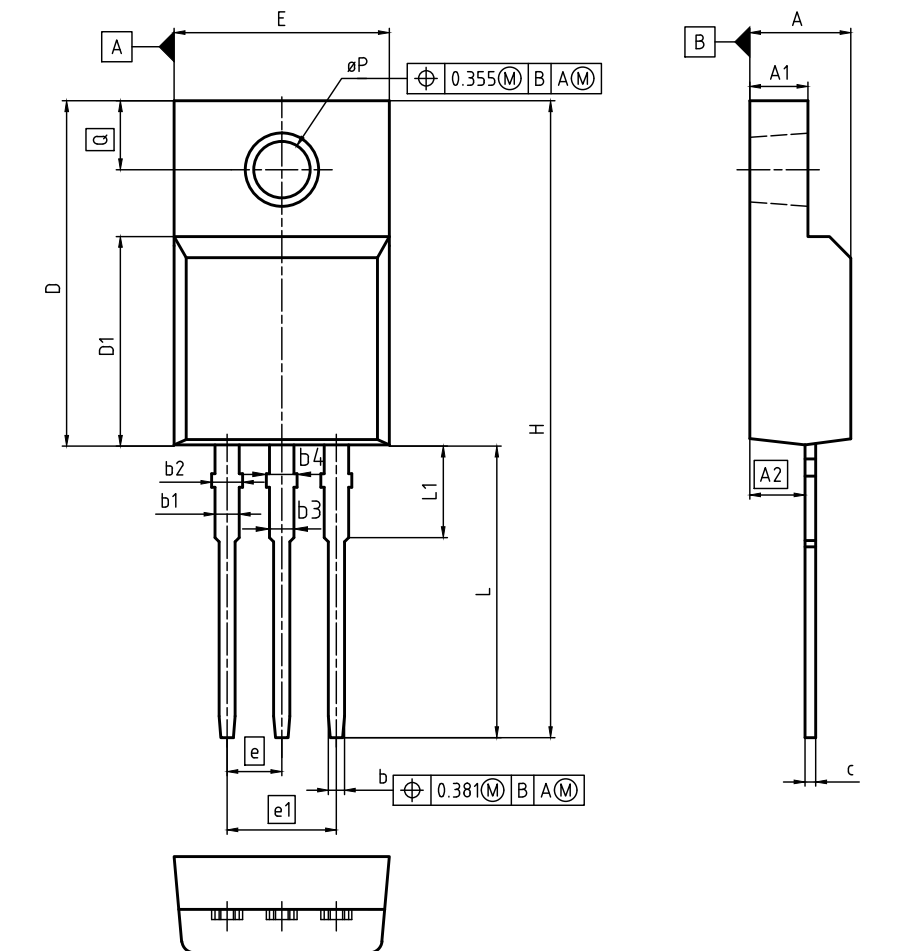


Figure 2 Outline PG-TO 220, dimensions in mm/inches



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.34	2.85	0.092	0.112
A2	2.42	2.86	0.095	0.113
b	0.65	0.90	0.026	0.035
b1	0.95	1.38	0.037	0.054
b2	0.95	1.51	0.037	0.059
b3	0.65	1.38	0.026	0.054
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.67	16.15	0.617	0.636
D1	8.97	9.83	0.353	0.387
E	10.00	10.65	0.394	0.419
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	3		3	
H	28.70	29.75	1.130	1.171
L	12.78	13.75	0.503	0.541
L1	2.83	3.45	0.111	0.136
øP	2.95	3.38	0.116	0.133
Q	3.15	3.50	0.124	0.138

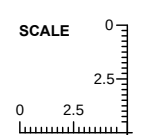
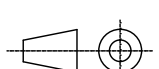
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EUROPEAN PROJECTION 	
ISSUE DATE 05-05-2014	
REVISION 04	

Figure 3 Outline PG-TO 220 FullPAK, dimensions in mm/inches

8 Appendix A

Table 12 Related Links

- IFX CoolMOS™ P6 Webpage: www.infineon.com
- IFX CoolMOS™ P6 application note: www.infineon.com
- IFX CoolMOS™ P6 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPW60R099P6, IPP60R099P6, IPA60R099P6

Revision: 2015-05-18, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-03-07	Release of final version
2.1	2015-05-18	Rdson max change from 105 to 99mOhm

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Infineon Technologies AG

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